

SPTECH Silicon PNP Power Transistor

2N6476

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 15-150 @ I_C = -1.5A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- Complement to Type 2N6474

APPLICATIONS

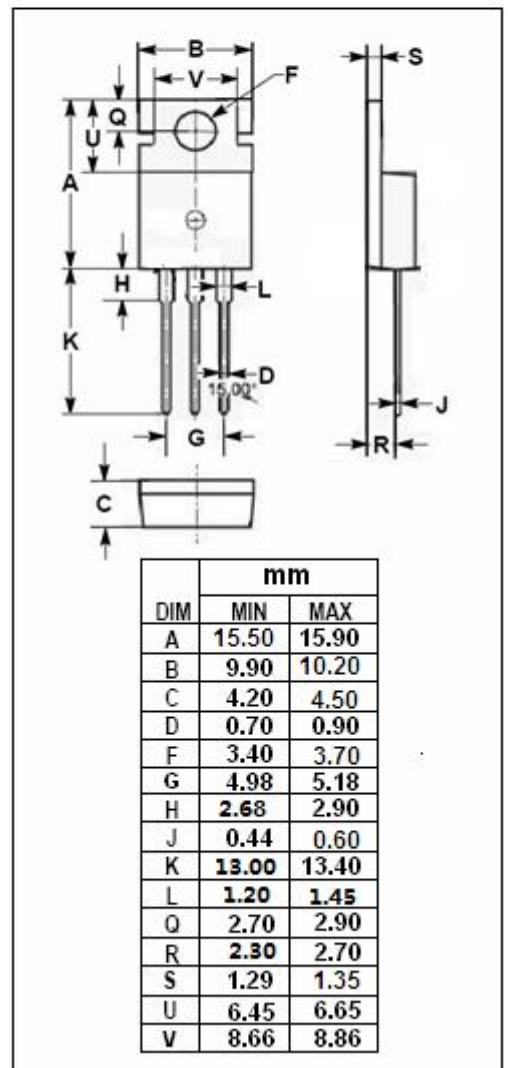
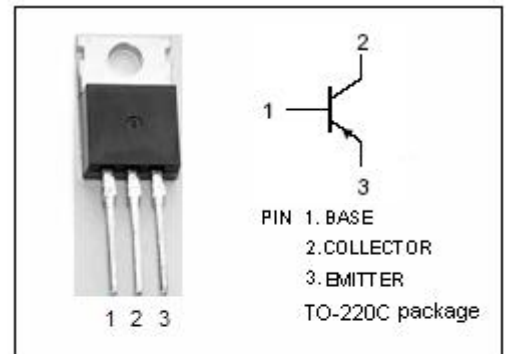
- Designed for general-purpose amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-130	V
V_{CER}	Collector-Emitter Voltage $R_{BE} = 100\ \Omega$	-130	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_B	Base Current	-2	A
P_D	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.125	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}$; $I_B = 0$	-120		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -1.5\text{A}$; $I_B = -0.15\text{A}$		-1.2	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -2\text{A}$		-2.5	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	$I_C = -1.5\text{A}$; $V_{CE} = -4\text{V}$		-2.0	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	$I_C = -4\text{A}$; $V_{CE} = 2.5\text{V}$		-3.5	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}$; $I_B = 0$		-1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$		-1.0	mA
h_{FE-1}	DC Current Gain	$I_C = -1.5\text{A}$; $V_{CE} = -4\text{V}$	15	150	
h_{FE-2}	DC Current Gain	$I_C = -4\text{A}$; $V_{CE} = -2.5\text{V}$	2		
C_{OB}	Collector Output Capacitance	$I_E = 0$; $V_{CB} = -10\text{V}$; $f_{\text{test}} = 1\text{MHz}$		250	pF
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -4\text{V}$	5		MHz